

RGTH40TS65

650V 20A Field Stop Trench IGBT

V_{CES}	650V
I _{C(100°C)}	20A
V _{CE(sat) (Typ.)}	1.6V
P_D	144W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

Applications

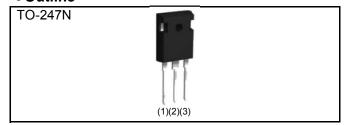
PFC

UPS

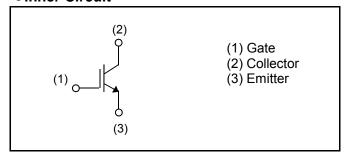
Power Conditioner

ΙH

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Typo	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing code	C11
	Marking	RGTH40TS65

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	T _C = 25°C	I _C	40	А
Collector Current	T _C = 100°C	I _C	20	А
Pulsed Collector Current		I _{CP} *1	80	А
$T_C = 25^{\circ}C$		P _D	144	W
Power Dissipation $T_C = 100^{\circ}C$		P _D	72	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{jmax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei		Min.	Тур.	Max.	Uill
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	1.04	°C/W

ullet IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r ai ainetei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	1	1	V
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	ı	1	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	V_{GE} = ±30V, V_{CE} = 0V	1	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	V _{CE} = 5V, I _C = 13.3mA	4.5	5.5	6.5	V
Collector - Emitter Saturation	$V_{CE(sat)}$	$I_C = 20A, V_{GE} = 15V$ $T_i = 25^{\circ}C$	_	1.6	2.1	V
Voltage	▼ CE(sat)	T _j = 175°C	-	2.1	-	v

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Darameter	Cymbol	Conditions	Values			Linit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C_{ies}	V _{CE} = 30V	-	1060	-	
Output Capacitance	C _{oes}	V _{GE} = 0V	-	47	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	18	-	
Total Gate Charge	Q_g	V _{CE} = 300V	-	40	-	
Gate - Emitter Charge	Q_{ge}	I _C = 20A	-	9	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	15	-	
Turn - on Delay Time	t _{d(on)}	I _C = 20A, V _{CC} = 400V	-	22	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	25	-	
Turn - off Delay Time	$t_{d(off)}$	T _j = 25°C	-	73	-	ns
Fall Time	t _f	Inductive Load	-	48	-	
Turn - on Delay Time	t _{d(on)}	I _C = 20A, V _{CC} = 400V	-	22	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	25	-	20
Turn - off Delay Time	$t_{d(off)}$	T _j = 175°C	-	83	-	ns
Fall Time	t _f	Inductive Load	-	58	-	
		I _C = 80A, V _{CC} = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FU	LL SQUA	RE	-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

•Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

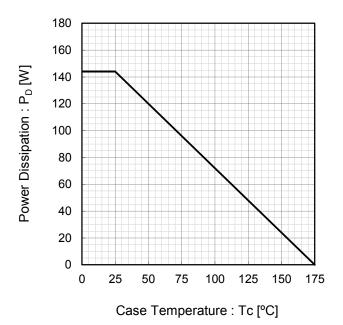


Fig.2 Collector Current vs. Case Temperature

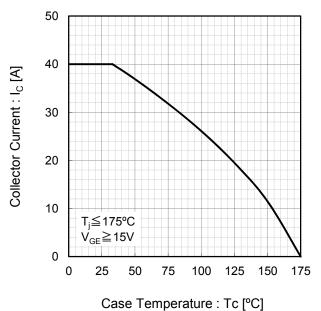
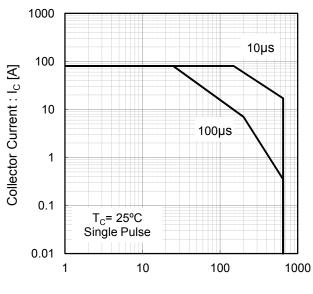
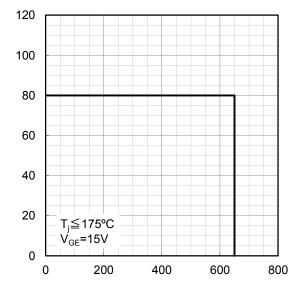


Fig.3 Forward Bias Safe Operating Area



Collector To Emitter Voltage : $V_{CE}[V]$

Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage : $V_{CE}[V]$

Collector Current : I_C [A]

• Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

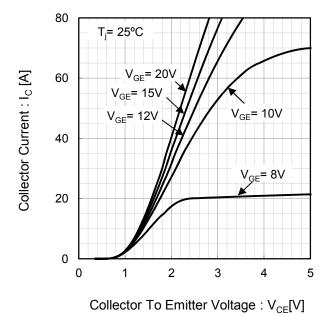
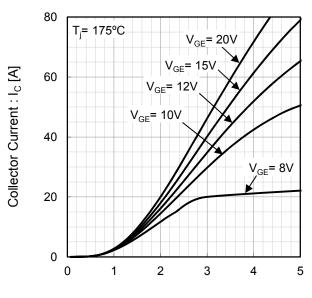


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : $V_{CE}[V]$

Fig.7 Typical Transfer Characteristics

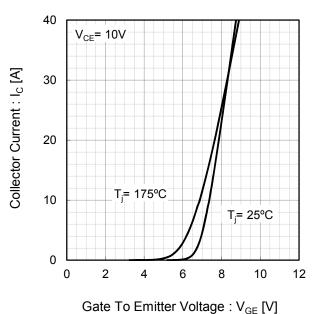
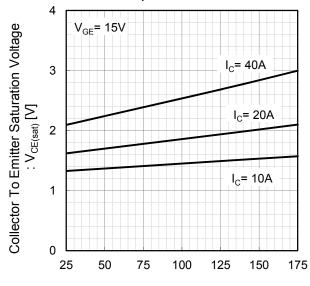


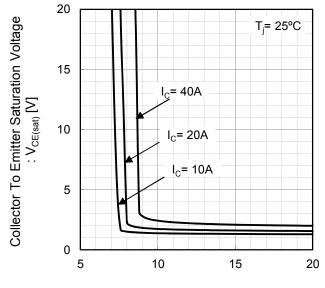
Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

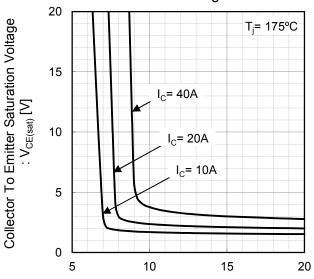
Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V_{GE} [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V_{GE} [V]

Fig.11 Typical Switching Time vs. Collector Current

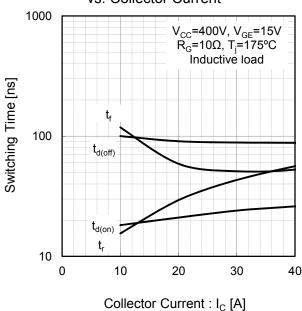
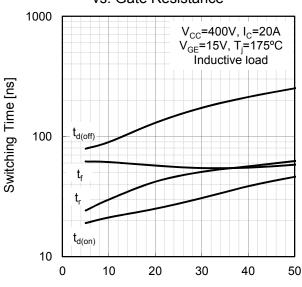


Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance : $R_G[\Omega]$

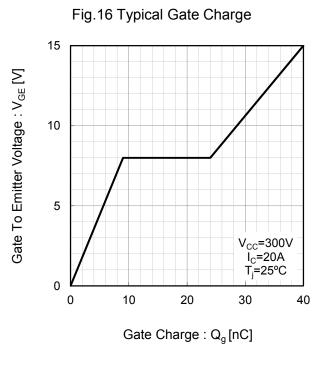
•Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ 0.1 E_{on} V_{CC} =400V, V_{GE} =15V R_{G} =10 Ω , T_{j} =175°C Inductive load 0.01 0 10 20 30 40 Collector Current : I_C [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] 1 E_{off} E_{on} 0.1 V_{CC}=400V, I_C=20A V_{GE}=15V, T_j=175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

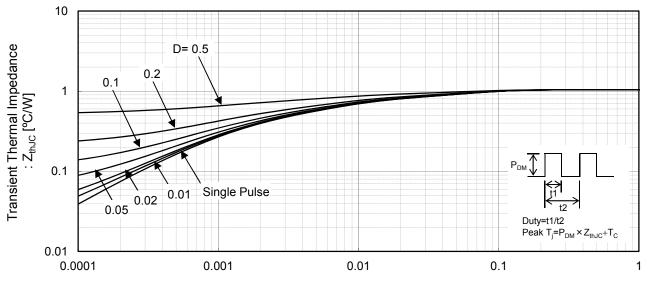
Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V_{GE}=0V =25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V_{CE}[V]



•Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

●Inductive Load Switching Circuit and Waveform

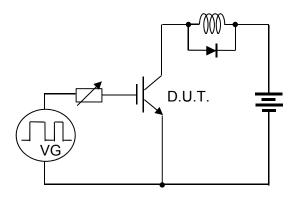


Fig.18 Inductive Load Circuit

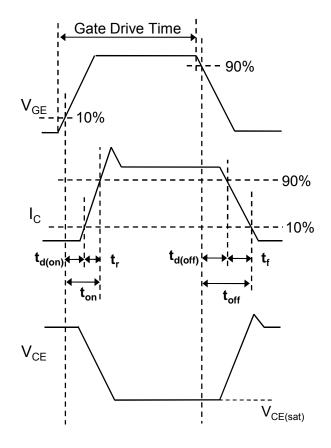


Fig.19 Inductive Load Waveform

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RGTH40TS65 - Web Page

Distribution Inventory

Part Number	RGTH40TS65
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	450
Packing Type	Bulk
Constitution Materials List	inquiry
RoHS	Yes

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 APT70GR120J
 APT35GP120JDQ2

 IKFW40N65ES5XKSA1
 IMBG120R220M1HXTMA1
 XD15H120CX1
 XD25H120CX0
 XP15PJS120CL1B1
 IGW30N60H3FKSA1

 STGWA8M120DF3
 IGW08T120FKSA1
 IGW75N60H3FKSA1
 HGTG40N60B3
 FGH60N60SMD_F085
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 IKA10N60TXKSA1
 IKW25N120T2FKSA1
 IKP20N60TXKSA1
 IHW20N65R5XKSA1
 IDW40E65D2FKSA1

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